

Zener Diodes, 24 and 40 Watt Peak Power

SOT-23 Dual Common Anode Zeners

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage ESD protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range – 5.6 V to 47 V
- Peak Power – 24 or 40 W @ 1.0 ms (Unidirectional), per Figure 6 Waveform
- ESD Rating:
 - Class 3B (> 16 kV) per the Human Body Model
 - Class C (> 400 V) per the Machine Model
 - IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Low Leakage < 5.0 μ A
- Flammability Rating UL 94 V-0
- 175°C T_{J(MAX)} – Rated for High Temperature, Mission Critical Applications
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

Package designed for optimal automated board assembly

Small package size for high density applications

Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel.

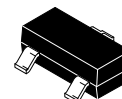
Replace the “T1” with “T3” in the Device Number to order the

13 inch/10,000 unit reel.

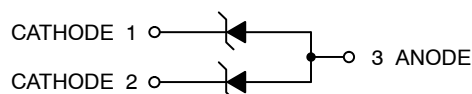


ON Semiconductor®

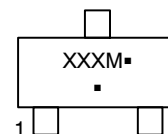
www.onsemi.com



SOT-23
CASE 318
STYLE 12



MARKING DIAGRAM



XXX = Specific Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 3 of this data sheet.

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) MMBZH5V6ALT1G thru MMBZH9V1ALT1G @ $T_L \leq 25^\circ\text{C}$ MMBZH12VALT1G thru MMBZH47VALT1G	P_{pk}	24 40	W
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.5	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	540	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to +175	$^\circ\text{C}$
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 6 and derate above $T_A = 25^\circ\text{C}$ per Figure 7.
2. FR-5 = 1.0 x 0.75 x 0.62 in.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBZHxVxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZHxVxALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZHxVxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZHxVxALT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZHxxVxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZHxxVxALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZHxxVxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZHxxVxALT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

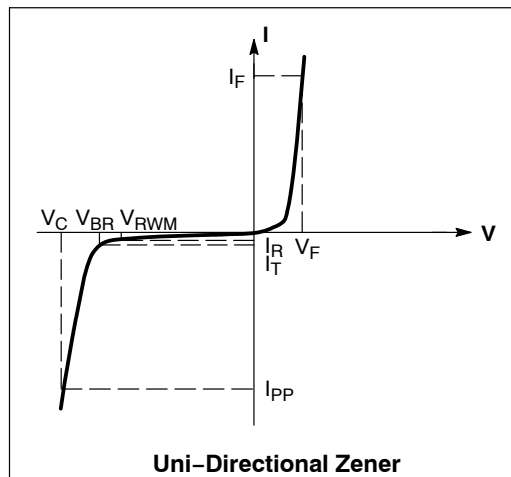
MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
ΘV _{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

(V_F = 0.9 V Max @ I_F = 10 mA) (5% Tolerance)

24 WATTS

Device*	Device Marking	V _{RWM} Volts	I _R @ V _{RWM} μA	Breakdown Voltage				Max Zener Impedance (Note 4)			V _C @ I _{PP} (Note 5)		ΘV _{BR} mV/°C
				V _{BR} (Note 3) (V)			@ I _T	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}	V _C	I _{PP}		
				Min	Nom	Max	mA	Ω	Ω	mA	V	A	
MMBZH5V6ALT1G**	5A6	3.0	5.0	5.32	5.6	5.88	20	11	1600	0.25	8.0	3.0	1.26
MMBZH6V2ALT1G**	6A2	3.0	0.5	5.89	6.2	6.51	1.0	—	—	—	8.7	2.76	2.80
MMBZH6V8ALT1G**	6A8	4.5	0.5	6.46	6.8	7.14	1.0	—	—	—	9.6	2.5	3.4
MMBZH9V1ALT1G**	9A1	6.0	0.3	8.65	9.1	9.56	1.0	—	—	—	14	1.7	7.5

(V_F = 0.9 V Max @ I_F = 10 mA) (5% Tolerance)

40 WATTS

Device*	Device Marking	V _{RWM}	I _R @ V _{RWM}	Breakdown Voltage				V _C @ I _{PP} (Note 5)		ΘV _{BR}
				V _{BR} (Note 3) (V)			@ I _T	V _C	I _{PP}	
		Volts	nA	Min	Nom	Max	mA	V	A	
MMBZH12VALT1G**	12A	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5
MMBZH15VALT1G**	15A	12	50	14.25	15	15.75	1.0	21	1.9	12.3
MMBZH16VALT1G**	16A	13	50	15.20	16	16.80	1.0	23	1.7	13.8
MMBZH18VALT1G	ACJ	14.5	50	17.10	18	18.90	1.0	25	1.6	15.3
MMBZH20VALT1G**	20A	17	50	19.00	20	21.00	1.0	28	1.4	17.2
MMBZH27VALT1G**	27A	22	50	25.65	27	28.35	1.0	40	1.0	24.3
MMBZH33VALT1G**	33A	26	50	31.35	33	34.65	1.0	46	0.87	30.4
MMBZH47VALT1G**	47A	38	50	44.65	47	49.35	1.0	54	0.74	43.1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.

4. Z_{ZT} and Z_{ZK} are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I_{Z(AC)} = 0.1 I_{Z(DC)}, with the AC frequency = 1.0 kHz.

5. Surge current waveform per Figure 6 and derate per Figure 7

* Includes SZ-prefix devices where applicable.

**AEC-Q release available upon request.

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

TYPICAL CHARACTERISTICS

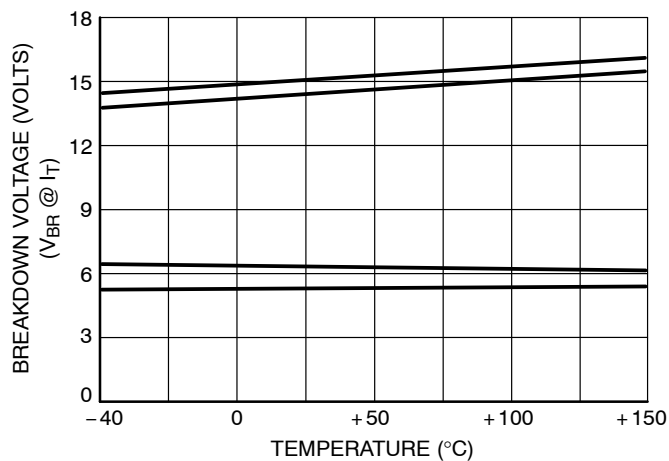


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

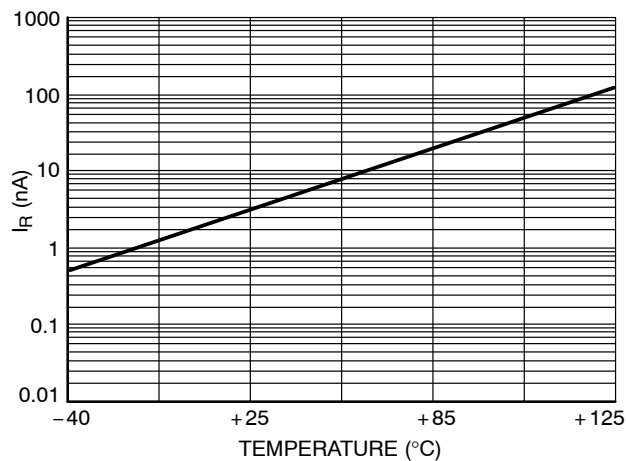


Figure 2. Typical Leakage Current versus Temperature

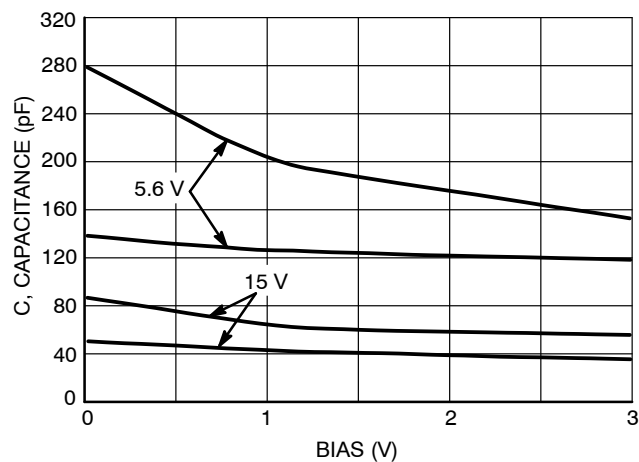


Figure 3. Typical Capacitance versus Bias Voltage

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

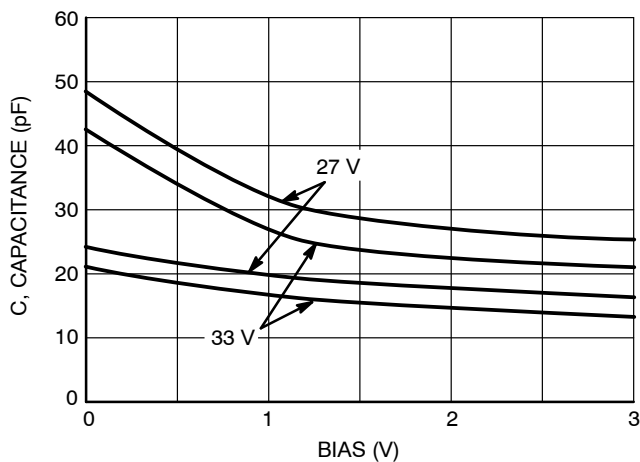


Figure 4. Typical Capacitance versus Bias Voltage

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

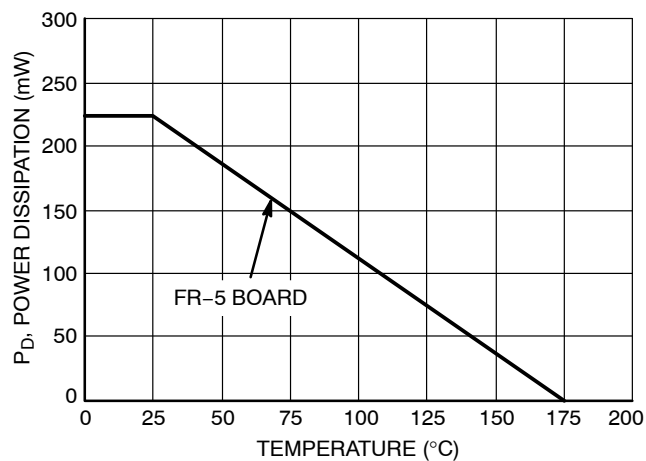


Figure 5. Steady State Power Derating Curve

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

TYPICAL CHARACTERISTICS

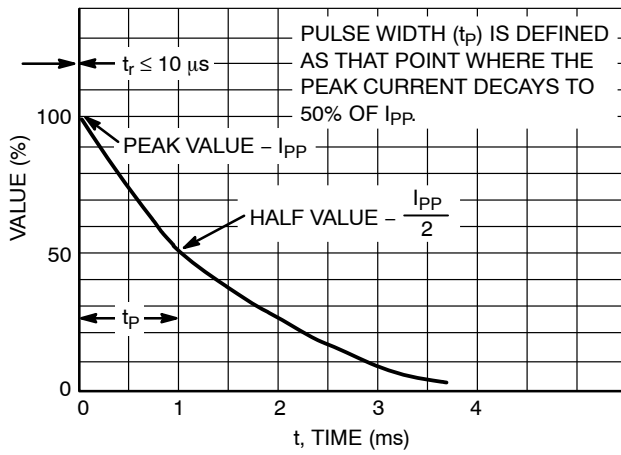


Figure 6. Pulse Waveform

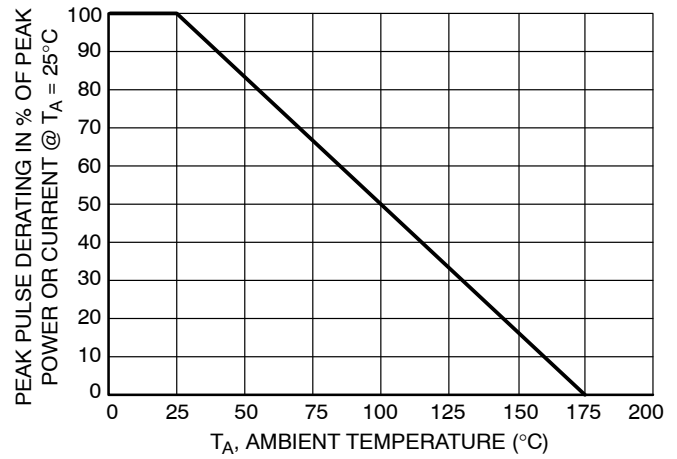


Figure 7. Pulse Derating Curve

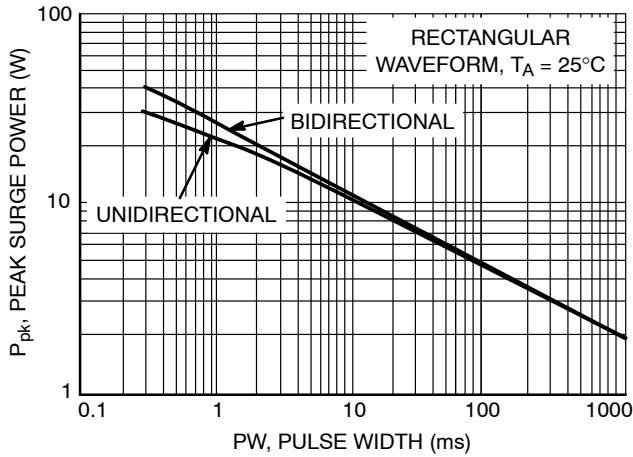


Figure 8. Maximum Non-repetitive Surge Power, P_{pk} versus PW

Power is defined as $V_{RSM} \times I_Z(pk)$ where V_{RSM} is the clamping voltage at $I_Z(pk)$.

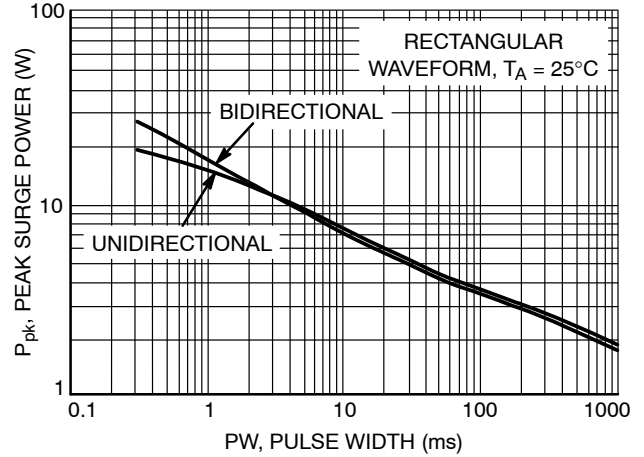


Figure 9. Maximum Non-repetitive Surge Power, $P_{pk(NOM)}$ versus PW

Power is defined as $V_Z(NOM) \times I_Z(pk)$ where $V_Z(NOM)$ is the nominal Zener voltage measured at the low test current used for voltage classification.

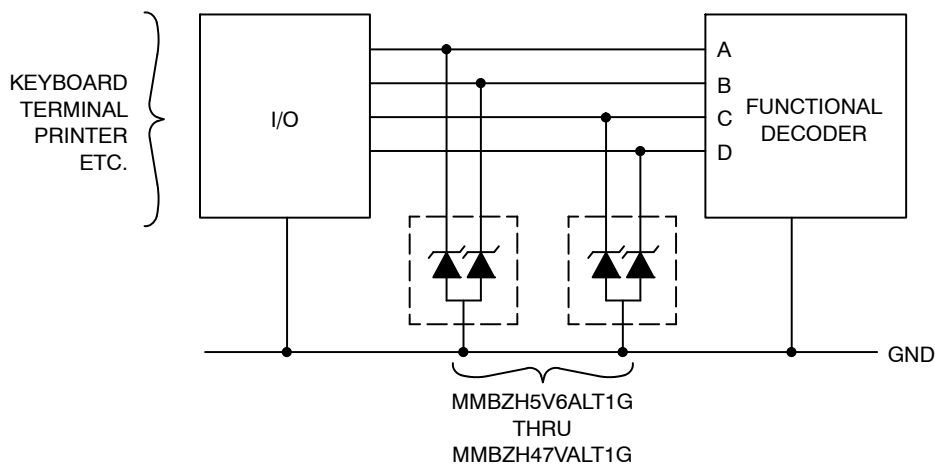
MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

TYPICAL COMMON ANODE APPLICATIONS

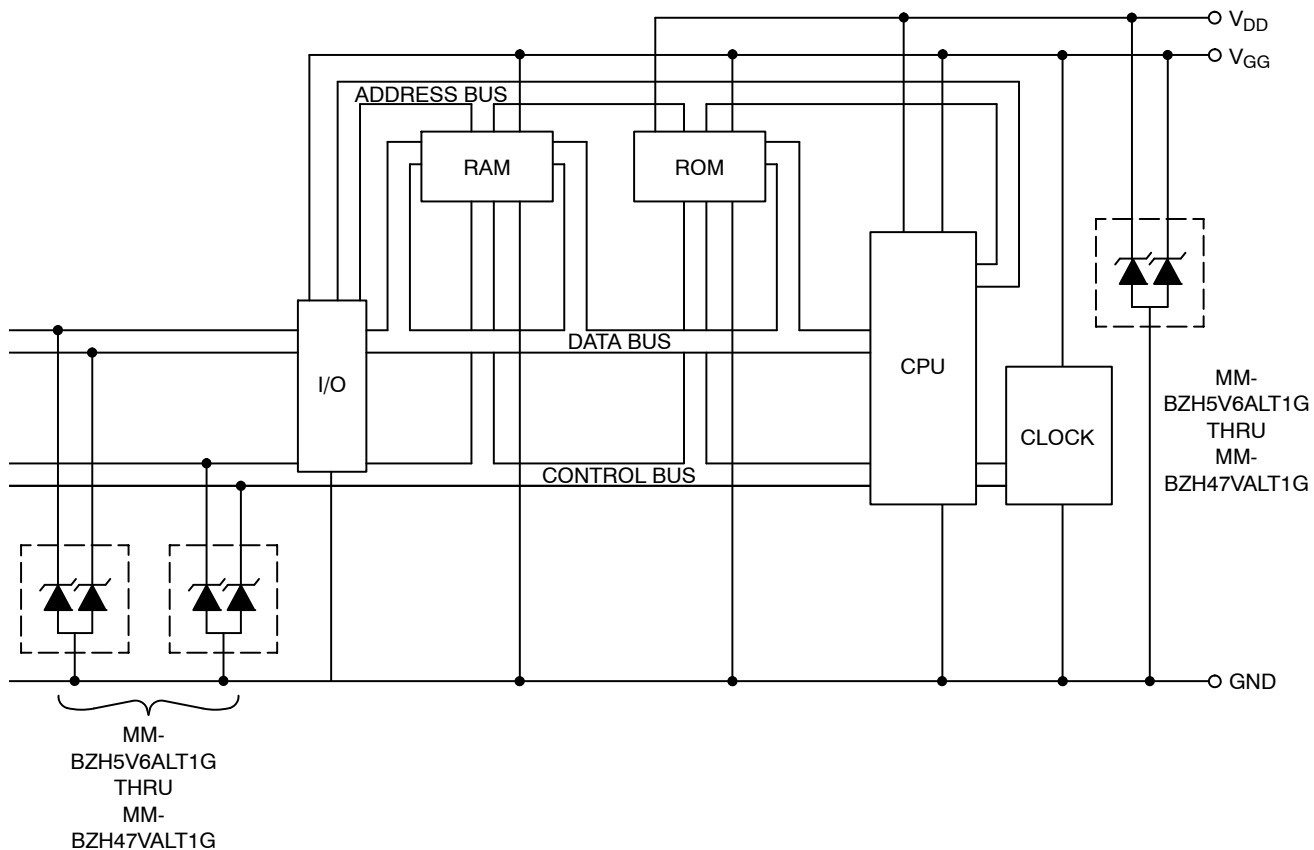
A dual junction common anode design in a SOT-23 package protects two separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of ESD applications are illustrated below.

Computer Interface Protection



Microprocessor Protection



onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales